Abstracts

A 6-18 GHz 20 W SPDT switch using shunt discrete PIN diodes

T. Shigematsu, N. Suematsu, N. Takeuchi, Y. Iyama and A. Mizobuchi. "A 6-18 GHz 20 W SPDT switch using shunt discrete PIN diodes." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 527-530.

A broadband high power SPDT switch using shunt discrete PIN diodes is presented. By using shunt SPDT switch configuration, high power performance can be obtained. A novel structure, in which matching sections are added outside of shunt PIN diodes, provides broadband characteristics. The insertion loss of the fabricated MIC switch is less than 2.0 dB at 6 to 18 GHz, and is less than 1.5 dB at 7 to 17 GHz. The power handling capability is over 20 W CW at 12 GHz.

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